

Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
 STATEMENT BY APPLICANT**

Application Number	10/719,663
Filing Date	November 20, 2003
First Named Inventor	Fanis
Group Art Unit	2818
Examiner Name	Nguyen, Dao H
Sheet 1 of 6	Attorney Docket Number
	Reveo-0202USAAON00

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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOC. NO.	DOCUMENT NUMBER	DATE	NAMES	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DN		4,309,225	05-Jan-82	Fan et al.	148	1.5	
		4,370,176	25-Jan-83	Bruel	148	1.5	
		4,371,421	01-Feb-83	Fan et al.	166	624	
		4,471,003	11-Sep-84	Cann	427	34	
		4,479,846	30-Oct-84	Smith et al.	156	603	
				Ellenberger et al.	427	38	
		4,500,563	19-Feb-85		260	492.2	
		4,585,945	29-Apr-86	Bruel et al.	437	2	
		4,818,420	28-Mar-89	Bozler et al.	437	82	
		4,837,182	06-Jun-89	Bozler et al.	117	2	
		4,846,931	11-Jul-89	Gmitter et al.	156	633	
		4,883,581	28-Nov-89	Gmitter et al.	156	633	
		5,273,616	28-Dec-93	Bozler et al.	156	603	
		5,362,682	08-Nov-94	Bozler et al.	437	226	
		5,374,564	20-Dec-94	Bruel	437	24	
		5,453,153	26-Sep-95	Fan et al.	117	2	
		5,559,043	24-Sep-96	Bruel	437	424	
		5,588,994	31-Dec-96	Bozler et al.	117	89	
		5,876,752	14-Oct-97	Bozler et al.	117	89	
		5,710,057	20-Jan-98	Kenney	437	62	
		5,714,395	03-Feb-98	Bruel	437	24	
		5,793,115	11-Aug-98	Zavracky et al.	257	777	
		5,845,123	01-Dec-98	Johnson et al.	395	377	
		5,877,070	02-Mar-99	Goesele et al.	438	458	
		5,882,987	16-Mar-99	Srikrishnan	438	458	
		5,897,939	27-Apr-99	Deleonibus	428	195	
		5,909,627	01-Jun-99	Egloff	438	406	
		5,920,764	06-Jul-99	Hanson et al.	438	4	
		5,933,750	03-Aug-99	Wilson et al.	438	455	
		5,976,953	02-Nov-99	Zavracky et al.	438	455	
		5,985,688	16-Nov-99	Bruel	438	53	
		5,993,677	30-Nov-99	Biassé et al.	216	36	
		5,994,207	30-Nov-99	Henley et al.	438	515	
		6,020,252	01-Feb-00	Aspar et al.	438	458	
		6,027,988	22-Feb-00	Cheung et al.	483	513	
		6,033,974	07-Mar-00	Henley et al.	438	526	
		6,054,383	25-Apr-00	Sakaguchi et al.	438	406	
		6,054,370	25-Apr-00	Doyle	438	456	
		6,059,877	09-May-00	Bruel	117	35	
		6,071,795	08-Jun-00	Cheung et al.	438	458	
		6,103,597	15-Aug-00	Aspar et al.	438	458	
DN		6,137,110	24-Oct-00	Pellin et al.	250	423	

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	Group Art Unit	2818
	Examiner Name	Nguyen, Dao H
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EXAMINER INITIAL	DOC. NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DN		6,148,979	14-Nov-00	Henley et al.	438	458	
		6,155,909	05-Dec-00	Henley et al.	451	39	
		6,159,323	12-Dec-00	Joly et al.	156	241	
		6,159,824	12-Dec-00	Henley et al.	438	455	
		6,159,825	12-Dec-00	Henley et al.	438	460	
		6,162,705	19-Dec-00	Henley et al.	438	478	
		6,184,060	06-Feb-01	Siniaguine	438	106	
		6,184,111	06-Feb-01	Henley et al.	438	514	
		6,187,110	13-Feb-01	Henley et al.	148	33.2	
		6,190,937	20-Feb-01	Nakagawa et al.	438	67	
		6,190,998	20-Feb-01	Bruel et al.	438	407	
		6,191,007	20-Feb-01	Matsui et al.	438	459	
		6,204,151	20-Mar-01	Malik et al.	438	460	
		6,214,733	10-Apr-01	Sickmiller	438	691	
		6,221,738	24-Apr-01	Sakaguchi et al.	438	455	
		6,221,740	24-Apr-01	Bryan et al.	438	458	
		6,221,774	24-Apr-01	Malik	438	690	
		6,225,190	01-May-00	Bruel et al.	438	458	
		6,225,192	01-May-00	Aspar et al.	438	460	
		6,232,136	15-May-01	Zavracky et al.	438	30	
		6,387,736	May 2002	Cao et al.	438	149	
DN		6,309,945	Oct 2001	Sato	437	409	

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
DN	EP0355913A1	28-Feb-90	Europe				
	WO 95/20824A1	3-Aug-95	PCT				
	WO 98/20543A2	14-May-98	PCT				
	WO 98/33209	30-Jul-98	PCT				
	WO 99/05711A1	4-Feb-99	PCT				
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	WO 99/39377A1	5-Aug-99	PCT				
	WO 99/66559A1	23-Dec-99	PCT				
	WO 00/03429A1	20-Jan-00	PCT				
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	WO 00/48238A1	17-Aug-00	PCT				
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		Group Art Unit 2818
		Examiner Name Nguyen, Dao H
Sheet 4 of 6		Attorney Docket Number Reveo-0202USAAON00

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